

MICRON.092CP1



PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Stephen L. Willis ✓) Group Art Unit 2815
Appl. No. : 09/552,383 ✓)
Filed : April 19, 2000 ✓)
For : CHEMICAL MECHANICAL)
PLANARIZATION OF)
CONDUCTIVE MATERIAL)
Examiner : Jose R. Diaz)

Sublee 2/25/03

#12/E
And
N/E

J. McMillon
1/7/03

RECEIVED
JAN - 7 2003
TECHNOLOGY CENTER 2800

AMENDMENT AFTER FINAL

Assistant Commissioner for Patents
Washington, D.C. 20231

Dear Sir:

In response to the Final Office Action mailed November 4, 2002, please amend the above-captioned application as follows.

IN THE CLAIMS:

Please, amend Claims 30 and 56 as follows:

30. (Amended) A method of forming a dielectric layer of a first thickness on a semiconductor wafer comprising:

forming the dielectric layer of the first thickness on the wafer;
positioning a shield layer on the dielectric layer;
positioning a sacrificial layer on the shield layer;
depositing conductive material on the sacrificial layer;

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